

## **User Guide**

## TDINV3000W050: 3.0 kW Inverter Evaluation Board

#### Introduction



Figure 1. TDINV3000W050 0v1 inverter evaluation board

### Warning



This evaluation board is intended to demonstrate GaN FET technology and is for demonstration purposes only and no guarantees are made for standards compliance.

There are areas of this evaluation board that have exposed access to hazardous high voltage levels. Exercise caution to avoid contact with those voltages. Also note that the evaluation board may retain high voltage temporarily after input power has been removed. Exercise caution when handling.

When testing converters on an evaluation board, ensure adequate cooling. Apply cooling air with a fan blowing across the converter or across a heatsink attached to the converter. Monitor the converter temperature to ensure it does not exceed the maximum rated per the datasheet specification.

The control portion of the circuit is designed around the popular C2000™ family of microcontrollers from Texas Instruments (TI). The source code is available along with related support information directly from TI. In addition to this general resource, Transphorm provides original firmware which comes loaded in flash on the microcontroller. The source code, configured as a complete project, is available at <a href="transphormusa.com/pv30kit">transphormusa.com/pv30kit</a>. This project is a convenient starting point for further developments. The microcontroller itself resides on a small, removable control card, supplied by TI, so that different C2000 devices may be used if desired. The schematic for the TDINV3000W050 circuit board is provided at the end of this user guide document, as well in the <a href="design files">design files</a>.

#### The TDINV3000W050-KIT includes:

- TDINV3000W050 single-phase inverter assembly
- Texas Instruments F28035 control card
- 12V power supply with U.S. adaptor

Complete design files, firmware files and support documentation can be found online at transphormusa.com/pv30kit.

### TDINV3000W050 input/output specifications

- High-voltage input: 420V<sub>DC</sub> max
- Auxiliary supply (J1): 12V<sub>CC</sub>
- Input: OV<sub>DC</sub> 420V<sub>DC</sub>
- Output: V<sub>DC</sub> / √2V<sub>RMS</sub> at 50/60Hz <sup>1</sup>, up to 3000W
- PWM frequency: 50kHz 200kHz<sup>2</sup>
- Power dissipation in the GaN FET is limited by the maximum junction temperature. Refer to the <u>TP65H050WS</u> datasheet

#### Circuit description

Refer to Figure 2 for a block diagram of the inverter circuit. A detailed schematic is available in the design files.

The TDINV3000W050 inverter is a simple full-bridge inverter. Two GaN half-bridges are driven with pulse-width modulated (PWM) command signals to create the sinusoidal varying output. The output filter largely removes the switching frequency, leaving the 50/60Hz fundamental sinusoid. The high-frequency (50kHz+) PWM signals are generated by the TI microcontroller and connected directly to high speed, high voltage gate drivers. A connection for external communication to the microcontroller is provided by an isolated USB interface. Except for the high-voltage supply for the power stage, all required voltages for the control circuitry are derived from one 12V input.



 $<sup>^{</sup>m 1}$  The output frequency may be changed in the software; as delivered it is  $60{\rm Hz}$ 

<sup>&</sup>lt;sup>2</sup> The switching frequency may be changed in the software; as delivered it is 50kHz

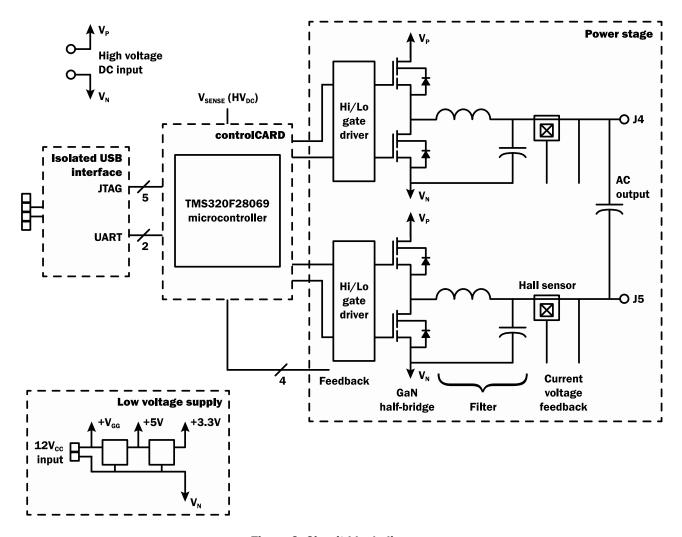


Figure 2. Circuit block diagram

The inverter takes advantage of diode-free operation, in which the freewheeling current is carried by the GaN FETs themselves due to their bi-directional capability, without the need of additional freewheeling diodes. For minimum conduction loss, the gates of the FETs are enhanced while they carry the freewheeling current. The high and low-side  $V_{GS}$  waveforms are therefore pairs of non-overlapping pulses, as illustrated in Figure 3 below.

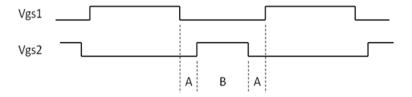


Figure 3. Non-overlapping gate-drive pulse; A is a dead time set in the firmware

### **Gate drivers**

High-voltage integrated drivers supply the gate-drive signals for the high and low-side GaN FETs. These are 2500V isolation drivers (Silicon Labs Si823x family), specifically chosen for high-speed operation without automatic dead time insertion. The dead time between turn-off of one GaN FET in a half-bridge and turn-on of its mate is set in the firmware.

### **Dead time control**

The required form of the gate-drive signals is shown in Figure 3. The times marked A are the dead times when neither transistor is driven on. The dead time must be greater than zero to avoid shoot-through currents. The Si8230 gate drive chip ensures a minimum dead time based on the value of resistor R24, connected to the AC input. The dead time in ns is equal to the resistance in  $k\Omega \times 10$ , so the default value of 12k corresponds to 120ns. This will add to any dead time already present in the input signals. The on-board pulse generator circuit; for example, creates dead times of about 100ns (see Figure 6). The resulting dead time at the gate pins of Q1 and Q2 is about 100ns. Either shorting or removing R4, R5 will reduce the dead time to 60ns.

### **Output filter**

A simple LC filter on the output (L1, L2, C43 and C44) attenuates the switching frequency, producing a clean sinusoidal waveform for output connections in terminals J4 and J5. The filter inductors and capacitors used on the demo board were chosen to provide the optional combination of benefits: low loss, good attenuation of the switching frequency, and small size. Consult the schematic and/or bill of materials to verify values; but in general, the cutoff frequency will be around 5kHz - 10kHz to accommodate 100Hz switching. The inductors have powder cores with relatively low permeability (60-90) and soft saturation characteristics. The inductors and/or capacitors can be changed to evaluate different filter designs.

### **Current sensing**

Hall sensors U5 and U6 provide linear current feedback to the microcontroller. These signals are used to control output power flow, to protect against over current. Note that these are placed at an intermediate point of the output filter. Refer to the bill of materials on page 7 to confirm the sensor part numbers, but typical would be the Allegro ACS723-20A sensor, which has a  $\pm 20A$  range (100mV/A). These parts are pin-compatible with a  $\pm 5A$  and  $\pm 30A$  versions of ACS723, should higher or lower ranges be desired. Note also that resistor dividers scale the 5V outputs for the 3V range of the A/D.

### Communication

Communication between the microcontroller and a computer is accomplished with a mini USB cable to a JTAG microcontroller interface.

#### **Control card**

The microcontroller resides on a removable card, which inserts in a DIM100 socket on the inverter PCB. The socket can accept many of the C2000 series control cards from Texas Instruments. The TMDSCNCD28035 Piccolo control card supplied with the kit provides capability to experiment with a wide variety of modulation and control algorithms. It comes loaded with firmware to allow immediate, out-of-the-box, operation. Should the user wish to use an alternative microcontroller family, an appropriate control card can be designed to insert into the DIM100 socket.

### Heatsink

The two TO-247 GaN FETs on each half-bridge are mounted on a common heatsink. The heatsink is adequate for 3000W operation with forced air flow. Even higher efficiency at high power may be achieved by minimizing the temperature rise. This may be accomplished with stronger airflow. Alternately the heatsinks could be replaced with larger and more effective ones.



### **Connections**

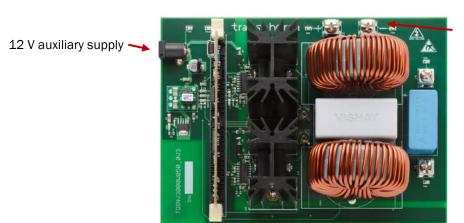
Power for the AC output is derived from the high-voltage DC input. This will typically be a DC power supply with output voltage up to  $420V_{DC}$ . A  $20\mu F$ , low ESR film capacitor is provided as a bypass capacitor for the high voltage supply, along with several lower valued ceramic capacitors in parallel. This is not intended to provide significant energy storage. It is assumed that the power supply or preceding DC-DC stage contains adequate output capacitance.

The control, communication, and gate-drive circuits are all powered from a single 12V input ( $V_{CC}$ ). The wall-plug adaptor provided generates the appropriate voltage (typically 12V) and power level.

Note that all signals on the board are referenced to the negative terminals of the high and low voltage supplies, which are tied together on the PCB. The heatsinks are also connected to the negative terminals of the supplies.

### Powering on the board

- Refer to Figure 4. Insert the microcontroller card to the DIM100 socket before applying any power to the board.
- Before turning on the supply, connect the high-voltage power supply to the +/- inputs (J2 and J3). DO NOT apply too much
  force to the J2 and J3 connectors, as excessive force may bend and/or crack the PCB.
- If a load is to be used, connect the load to the output terminals (J4 and J5). **DO NOT apply too much force to the J4 and J5** connectors, as excessive force may bend and/or crack the PCB.
- Insert the V<sub>CC</sub> (12V) plug to jack J1. LED1 should illuminate, indicating power is applied to the 5V and 3.3V regulators.
   Depending on the specific control card used, one or more LEDs on the control card will also illuminate, indicating power is applied. A flashing LED indicates the firmware is executing.
- To use the pre-loaded firmware, no computer connection is required. If a computer connection is required for code modification, connect the USB cable from the computer to the USB connector on the microcontroller.
- Turn on the high-voltage power. The high-voltage supply may be switched ON instantly or raised gradually.



High Voltage DC Supply

Figure 4. Connections

## Powering off the board

- 1. Switch off high-voltage DC supply
- 2. Power off 12V aux supply



## **Test overview**

Figure 5 shows typical waveforms. The negative terminal of the high-voltage supply is a convenient reference for the oscilloscope measurements, provided there are not multiple connections to earth ground.

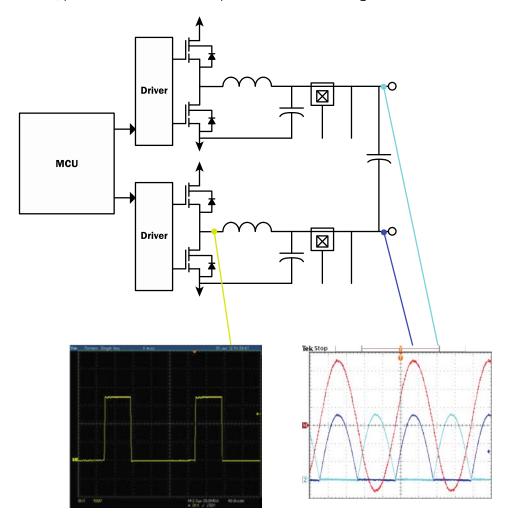


Figure 5. Typical waveforms

Typical efficiency results are shown in Figure 6. These data points correspond to efficiency measurements made in still air with 20 minutes' dwell at each power level. Input power from the 420V<sub>DC</sub> source and output power to a resistive load were measured with a Yokogawa WT1800 power analyzer.

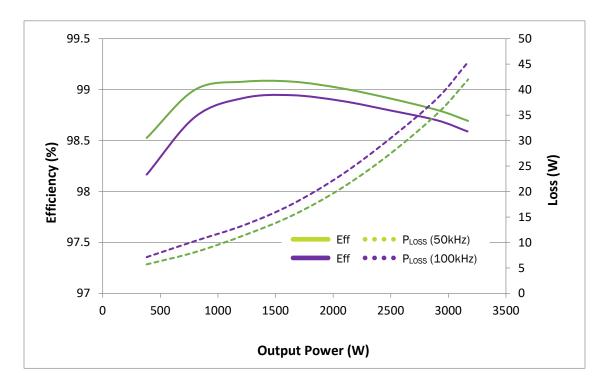


Figure 6. Typical efficiency: 420V<sub>DC</sub> input, 240V<sub>AC</sub> output

## **Design details**

See Figures 7 and 8 for a detailed circuit schematic and Figure 9 for the PCB layers (also included in the <u>design files</u>). The parts list can be found in Table 1.

Qty	Value	Device	Parts	Manf	Manf P/N	Dist P/N
2		530002B02500G	HS1, HS2	Aavid Thermalloy	530002B02500G	HS380-ND
4		KEYSTONE_7691	J2, J3, J4, J5	Keystone	7691	36-7691-ND
1		LEDCHIP- LED0805	LED1	Rohm	SML-211UTT86	511-1292-1-ND
1		PJ-002AH	J1	CUI Inc	PJ-002AH	CP-002AH-ND
2		TEKTRONIX-PCB	U_VDS, V_VDS	Tektronix	131-4353-00	131-4353-00
10		TESTPOINT- KEYSTONE5015	TP1, TP2, TP3, TP4, TP5, TP6, TP7, TP8, TP9, TP10	Keystone	5015	36-5015CT-ND
11	.1u	C-USC0603	C1, C13, C14, C15, C16, C19, C20,	AVX	06033C104JAT2A	478-3713-1-ND

Table 1. TDINV3000W050 evaluation board bill of materials (BOM)

			C21, C22, C25, C27			
4	.1u	C-USC0805	C8, C9, C10, C11	AVX	08053C104KAT2A	478-3755-1-ND
2	.1u	C-USC2225K	C43, C44	Vishay	VJ2225Y104KXGAT	720-1135-1-ND
1	0	R-US_R1206	R3	Panasonic	ERJ-8GEY0R00V	P0.0ECT-ND
8	1.6M	R-US_R1206	R33, R34, R35, R36, R37, R38, R39, R40	Panasonic	ERJ-8ENF1604V	P1.60MFCT-ND
4	10	R-US_R0805	R6, R7, R8, R9	Panasonic	ERJ-6GEYJ100V	P10ACT-ND
6	10	R-US_R1210	DCSNUB1, DCSNUB2, DCSNUB3, DCSNUB4, DCSNUB5, DCSNUB6	Yageo	AC1210FR-0710RL	YAG5426CT-ND
4	27	R-US_R0603	R10, R12, R14, R16	Rohm	ESR03EZPJ270	RHM27DCT-ND
2	10.2k	R-US_R0603	R19, R24	Panasonic	ERJ-3EKF1022V	P10.2KHCT-ND
2	100nF	C-EUC1206	C31, C32	Samsung Electronics	CL31F104MBCNNNC	1276-2854-1-ND
1	100pF (10v)	C-USC0603	C33	Wurth Electronics	885012006008	732-7752-1-ND
1	100u	PANASONICFPV	C3	Panasonic	EEE-FPE101XAP	PCE4546CT-ND
4	10k	R-US_R0603	R11, R13, R15, R17	Panasonic	ERJ-3GEYJ103V	P10KGCT-ND
5	10k	R-US_R1206	R41, R42, R43, R44, R51	Yageo	RC1206FR-0710KL	311-10.0KFRCT-ND
6	10n / 630V	C-EUC1206	C34, C35, C36, C38, C39, C40	Murata	GRM31BR72J103KW01L	490-3512-1-ND
4	<b>1</b> 0u	C-EUC0805	C17, C18, C23, C24	Kemet	C0805C106M4PACTU	399-8013-1-ND
1	10u	C-USC1206	C4	AVX	CL31A106KAHNNNE	1276-1075-1-ND
4	15	R-US_R1206	RSN1, RSN2, RSN3, RSN4	Stackpole	RNCP1206FTD15R0	RNCP1206FTD15R0CT-ND
1	1k	R-US_R0805	R1	Panasonic	ERJ-6GEYJ102V	P1.0KACT-ND
2	1n	C-USC0603	C26, C28	DNI	DNI	DNI
2	1n	C-USC0805	C7, C12	Yageo	CC0805KRX7R9BB102	311-1127-1-ND
2	220pF	C-EUC1206	C29, C30	Wurth Electronics	885012008014	732-7870-1-ND
4	47pF	C-EUC1206	CSN1, CSN2, CSN3, CSN4	Vishay	VJ1210A470JXGAT5ZL	720-1040-1-ND
1	22u	C-USC1206	C2	Samsung Electronics	CL31A226KAHNNNE	1276-3047-1-ND
1	2uF	2uF	C42	Epcos	B32674D6225K	495-2928-ND
1	348	R-US_R0805	R2	Panasonic	ERJ-6ENF3480V	P348CCT-ND
2	440UH_MPP	440UH_MPP	L1, L2	mps	440uH vertical inductor	440uH vertical inductor
2	5.23k	R-US_R0603	R18, R23	Panasonic	ERJ-3EKF5231V	P5.23KHCT-ND
2	12k	R-US_R0603	R4, R5	Yageo	RC0603FR-0712KL	311-12.0KHRCT-ND
4	560k	R-US_R1206	R20, R21, R25, R26	Yageo	RC1206FR-07560KL	311-560KFRCT-ND



4	680k	R-US_R1206	R28, R29, R30, R31	Panasonic	ERJ-P08J684V	P680KALCT-ND
3	9.09k	R-US_R1206	R22, R27, R32	Panasonic	ERJ-8ENF9091V	P9.09KFCT-ND
2	ACS723	ACS723	U5, U6	Allegro Microsystems	ACS723LLCTR-20AB-T	620-1644-1-ND
1	DIM100	DIM100	CN1	Texas Instruments	5390213-1	A121375-ND
1	22uF	22uF	C6	Vishay	MKP1848625454P4	BC2619-ND
1	OPA2350UA/2K5	OP_JC	U7	Texas Instruments	OPA2350UA/2K5	296-26258-1-ND
1	PTH08080WAH	PTH08080WAH	U2	ТІ	PTH08080WAH	296-20432-ND
2	SI82xx	SI8230	U3, U4	SiLabs	SI8230BB-D-IS	SI8230BB-D-IS-ND
4	TPP65H050WS	TPP65H050WS	Q1, Q2, Q3, Q4	TRANSPHORM	TPP65H050WS	TPP65H050WS
1	TPS79533	TPS79533	U1	TI	TPS79533DCQR	296-13810-1-ND
2	ES1J	DIODE-DO- 214AC	D1, D2	Fairchild	ES1J	ES1JFSCT-ND
2	THERMAL PAD	**BETWEEN TP65H050WS (Q1, Q3) AND HEATSINK	**BETWEEN TP65H050WS (Q1, Q3) AND HEATSINK	Aavid Thermalloy	4169G	4169G-ND
2	4-40 SCREW	"screw on TD65H050WS to heatsink	"screw on TD65H050WS to heatsink	B&F	PMSSS 440 0063 PH	H706-ND
2	4-40 NUT	Used to mount TP65H050WS to heatsink	Used to mount TP65H050WS to heatsink	keystone	9600	36-9600-ND
4	NYLON WASHER SHOULDER	used in between screw/nut and TP65H050WS	used in between screw/nut and TP65H050WS	keystone	3049	36-3049-ND
5	bumper cylin 0.312" dia blk	To place under PCB (5 locations: 4 each corner, 1 in the middle	To place under PCB (5 locations: 4 each corner, 1 in the middle	3M	SJ-5003 (BLACK)	SJ5003-0-ND
4	washer shoulder #6. To be installed between heatsink pins and PCB	washer shoulder #6. To be installed between heatsink pins and PCB	washer shoulder #6. To be installed between heatsink pins and PCB	keystone	7683	36-7683-ND
1	12Vdc aux supply	12Vdc aux supply	12Vdc aux supply	CUI Inc	SMI6-12-K-P5	102-3680-ND



1	CONTROL CARD PICCOLO ISO F28035	CONTROL CARD PICCOLO ISO F28035	CONTROL CARD PICCOLO ISO F28035	Texas Instruments	TMDSCNCD28035ISO	296-31058-ND
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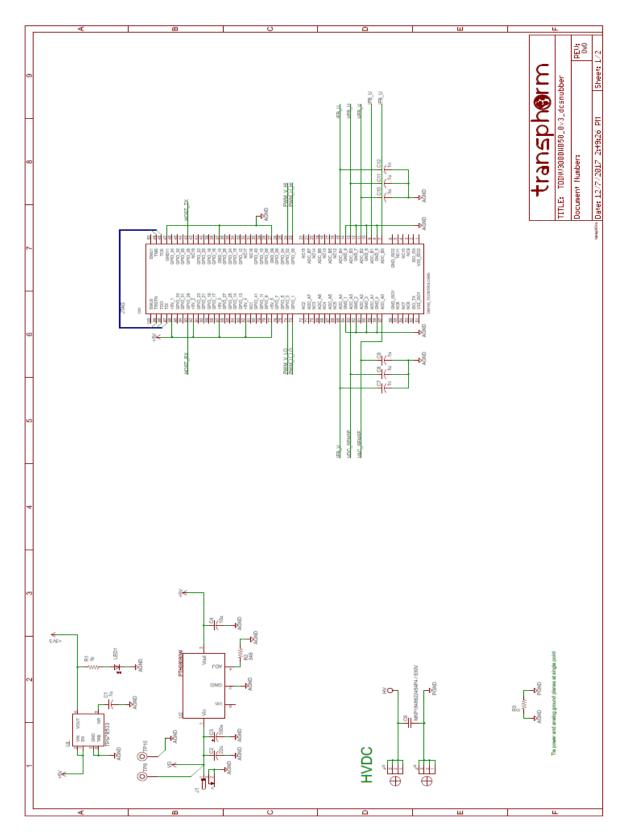


Figure 7. Detailed circuit schematic (1 of 2)

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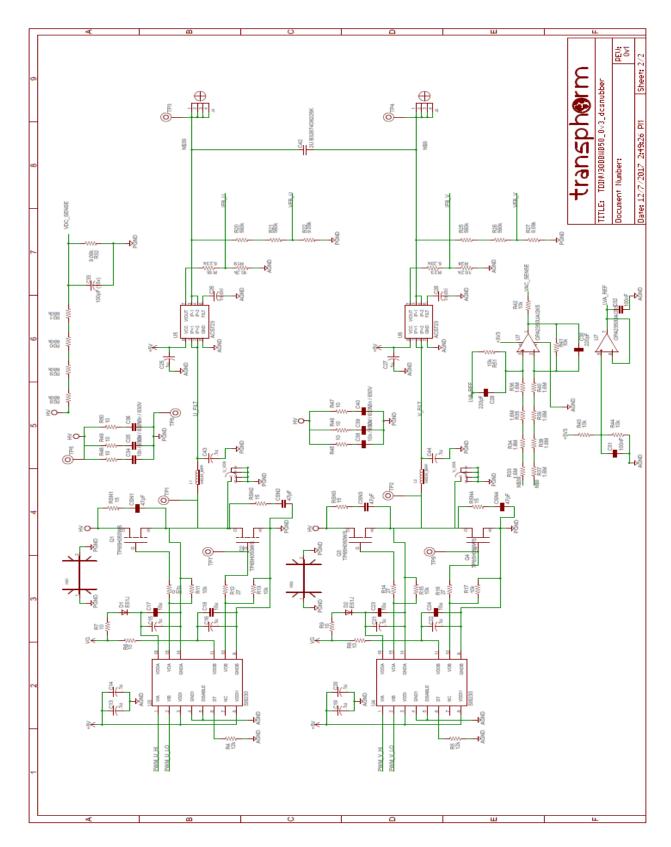
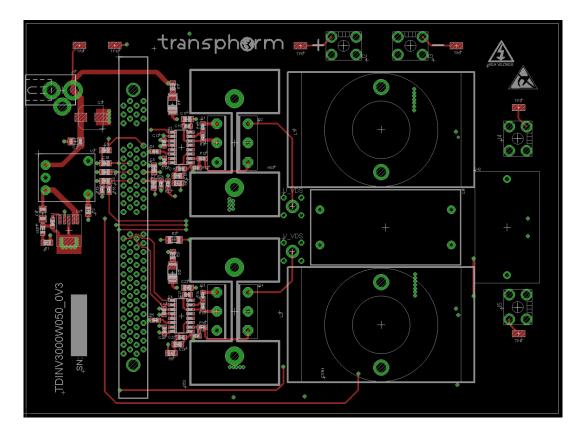
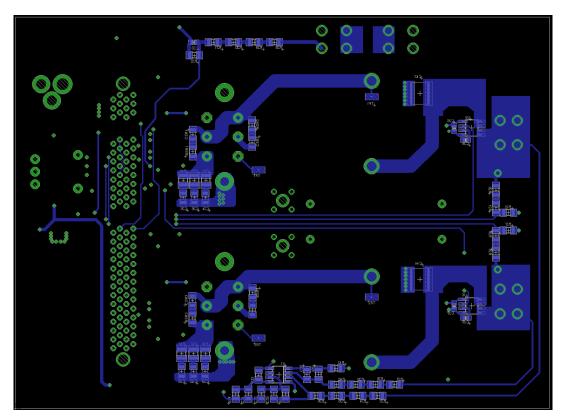


Figure 8. Detailed circuit schematic (2 of 2)

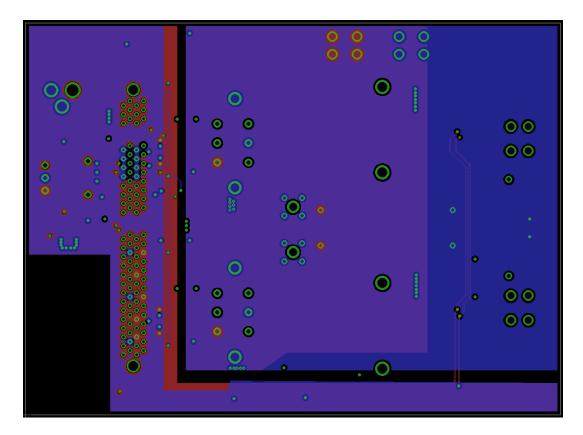


(a) PCB top layer



(b) PCB bottom layer





(c) PCB inner layer 2 (ground planes) and inner layer 3 (power plane)

Figure 9. PCB layers

## **Probing**

There are two available Tektronix test points on the PCB used to monitor the low-side switching (node) capability of each half-bridge circuit during operation.

The board has eight other test point locations for probing: Vcc, VDD, SN1, SN2, GS1, GS2, GND, GND.

To minimize inductance during measurement, the tip and the ground of the probe should be directly attached to the sensing points to minimize the sensing loop. For safe, reliable, and accurate measurement, a scope probe tip may be directly soldered to the low-side FET drain and a short ground wire soldered to the low-side FET source. See Figure 10 for an alternative that does not require soldering the probe tip.



Figure 10. Low-inductance probing of fast, high-voltage signals

#### **Protection features**

## **Under-voltage lockout**

The TDINV3000W050 evaluation board supports an under-voltage lockout feature. Be sure the feature is enabled if used. The board will blink red (LED LD2) on the control card in the event the board is in under-voltage and the output will be held off. When the under-voltage threshold is crossed, the output will be on and LED LD2 will be steady. The hysteresis value applies to the under-voltage trip threshold.

```
10 #define UNDER_VOLTAGE_ENABLE 0
11 #define UNDER_VOLTAGE_TRIP 10
12 #define HYSTERESIS_SET 5
13 #define OVER VOLTAGE TRIP 420
```

#### Over-voltage shutdown

The over-voltage feature is always enabled so be sure the overvoltage trip level is set high enough. In this example, the over-voltage threshold is 420V. In the event of an over-voltage event both red LEDs on the control card will blink in unison. The board must be powered down to recover from this type of event.

```
10 #define UNDER_VOLTAGE_ENABLE 0
11 #define UNDER_VOLTAGE_TRIP 10
12 #define HYSTERESIS_SET 5
13 #define OVER_VOLTAGE_TRIP 420
```

#### **Current limit shutdown**

The TDINV3000W050 evaluation board supports user-defined current limit thresholds in both the positive- and negative-going directions. The current limits are peak and in amps. In this example limits are set at 6.3A in both the positive- and negative-going directions. In most cases these trip points would be set to the same value. In an over-current event both red LEDs on the control card will blink in unison. The board must be powered down to recover from this type of event.

15 #define	COMPARATOR_MAX	20
16 #define	COMPARATOR_MIN	20